



US009059014B2

(12) **United States Patent**  
**Cheng et al.**

(10) **Patent No.:** **US 9,059,014 B2**  
(45) **Date of Patent:** **\*Jun. 16, 2015**

(54) **INTEGRATED CIRCUIT DIODE**

USPC ..... 257/368-369  
See application file for complete search history.

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(\*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 134 days.

This patent is subject to a terminal disclaimer.

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(21) Appl. No.: **13/870,220**

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(22) Filed: **Apr. 25, 2013**

*Assistant Examiner* — Ankush Singal

(65) **Prior Publication Data**

US 2013/0240998 A1 Sep. 19, 2013

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**Related U.S. Application Data**

(63) Continuation of application No. 13/104,542, filed on May 10, 2011, now Pat. No. 8,482,078.

(51) **Int. Cl.**

**H01L 21/70** (2006.01)

**H01L 27/07** (2006.01)

(Continued)

(57) **ABSTRACT**

A method includes forming isolation regions in a semiconductor substrate to define a first field effect transistor (FET) region, a second FET region, and a diode region, forming a first gate stack in the first FET region and a second gate stack in the second FET region, forming a layer of spacer material over the second FET region and the second gate stack, forming a first source region and a first drain region in the first FET region and a first diode layer in the diode region using a first epitaxial growth process, forming a hardmask layer over the first source region, the first drain region, the first gate stack and a portion of the first diode layer, and forming a second source region and a second drain region in the first FET region and a second diode layer on the first diode layer using a second epitaxial growth process.

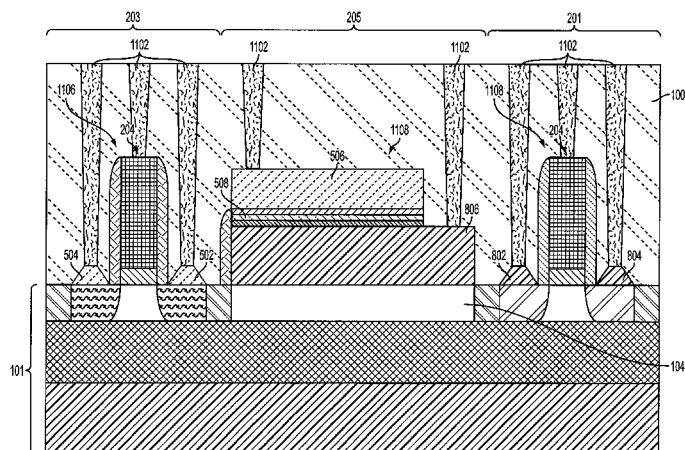
(52) **U.S. Cl.**

CPC .... **H01L 27/0727** (2013.01); **H01L 21/823418** (2013.01); **H01L 21/84** (2013.01); **H01L 27/0629** (2013.01); **H01L 27/1203** (2013.01)

(58) **Field of Classification Search**

CPC ..... H01L 27/0727

**7 Claims, 12 Drawing Sheets**



- (51) **Int. Cl.**  
**H01L 21/8234** (2006.01)  
**H01L 21/84** (2006.01)  
**H01L 27/06** (2006.01)  
**H01L 27/12** (2006.01)
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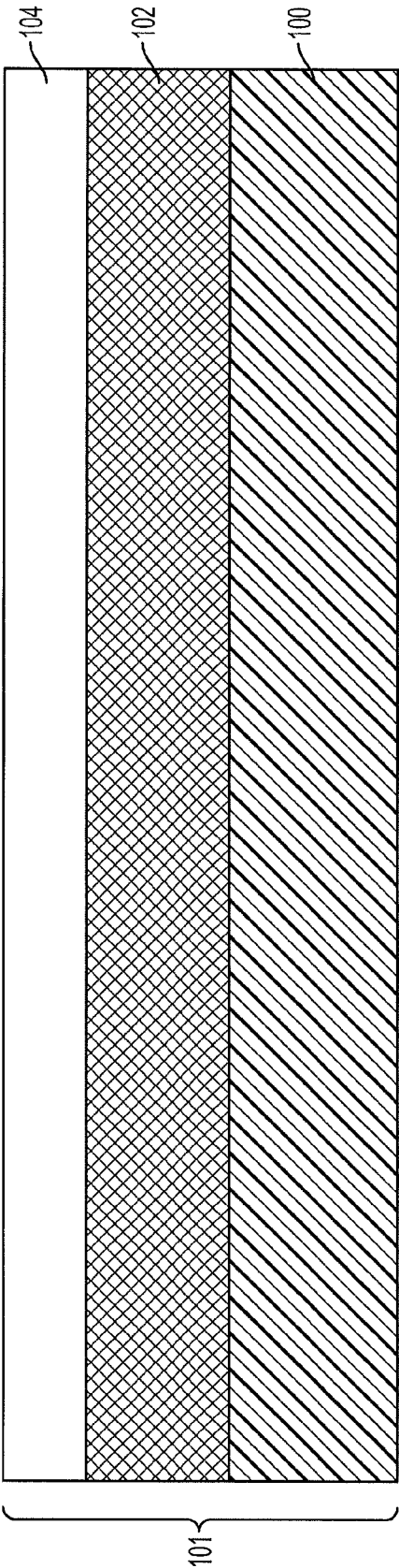


FIG. 1

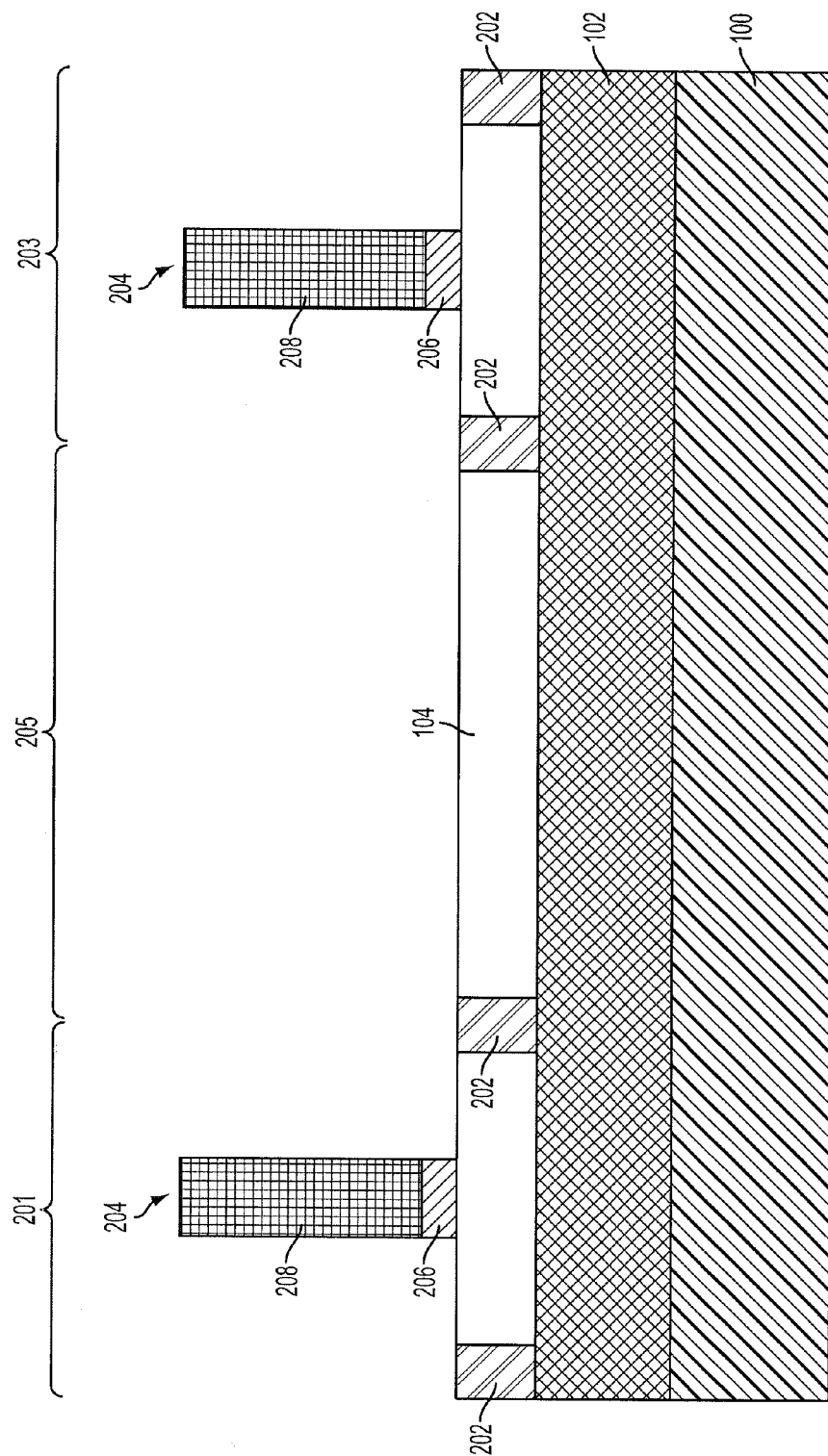


FIG. 2

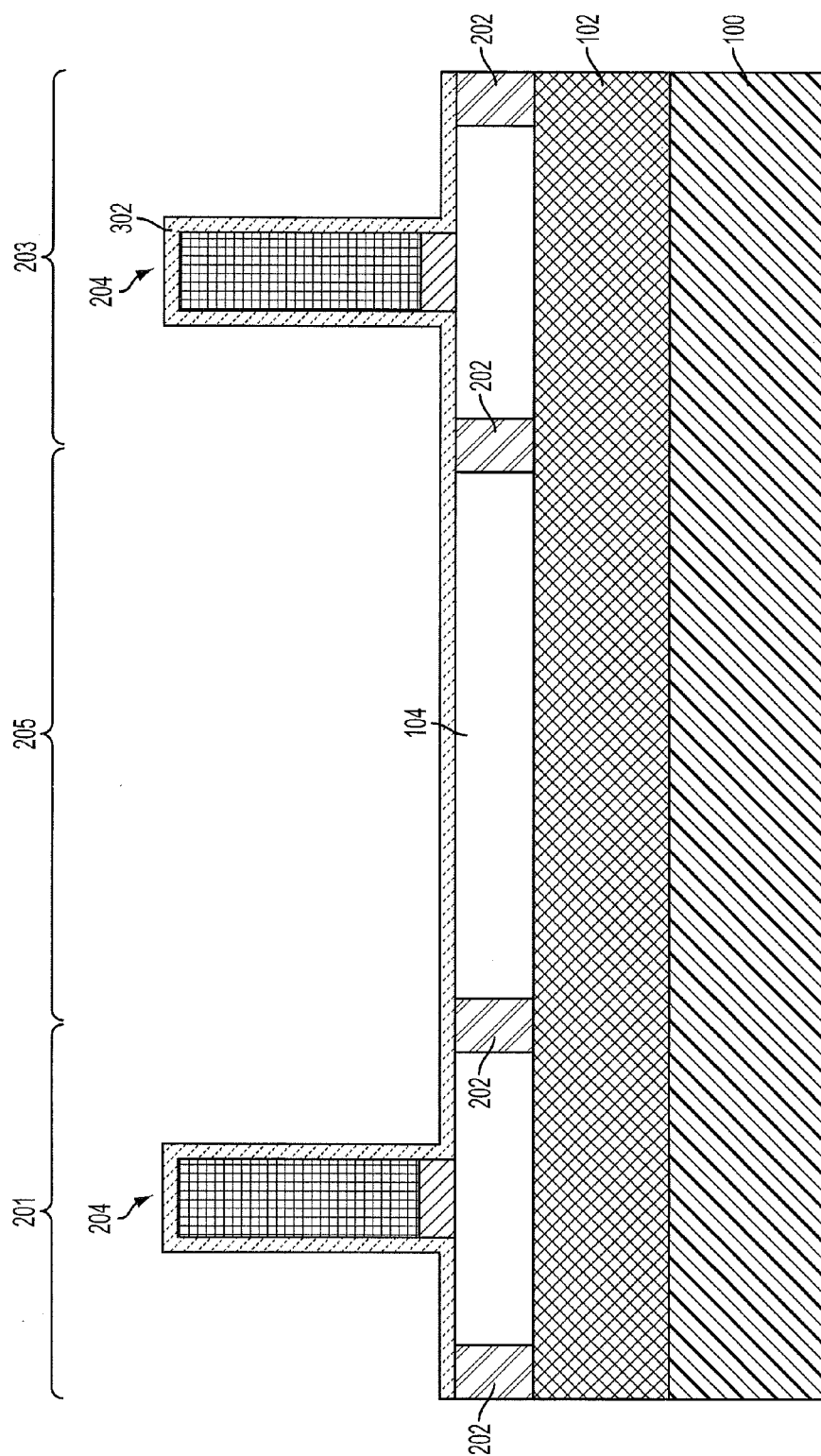


FIG. 3

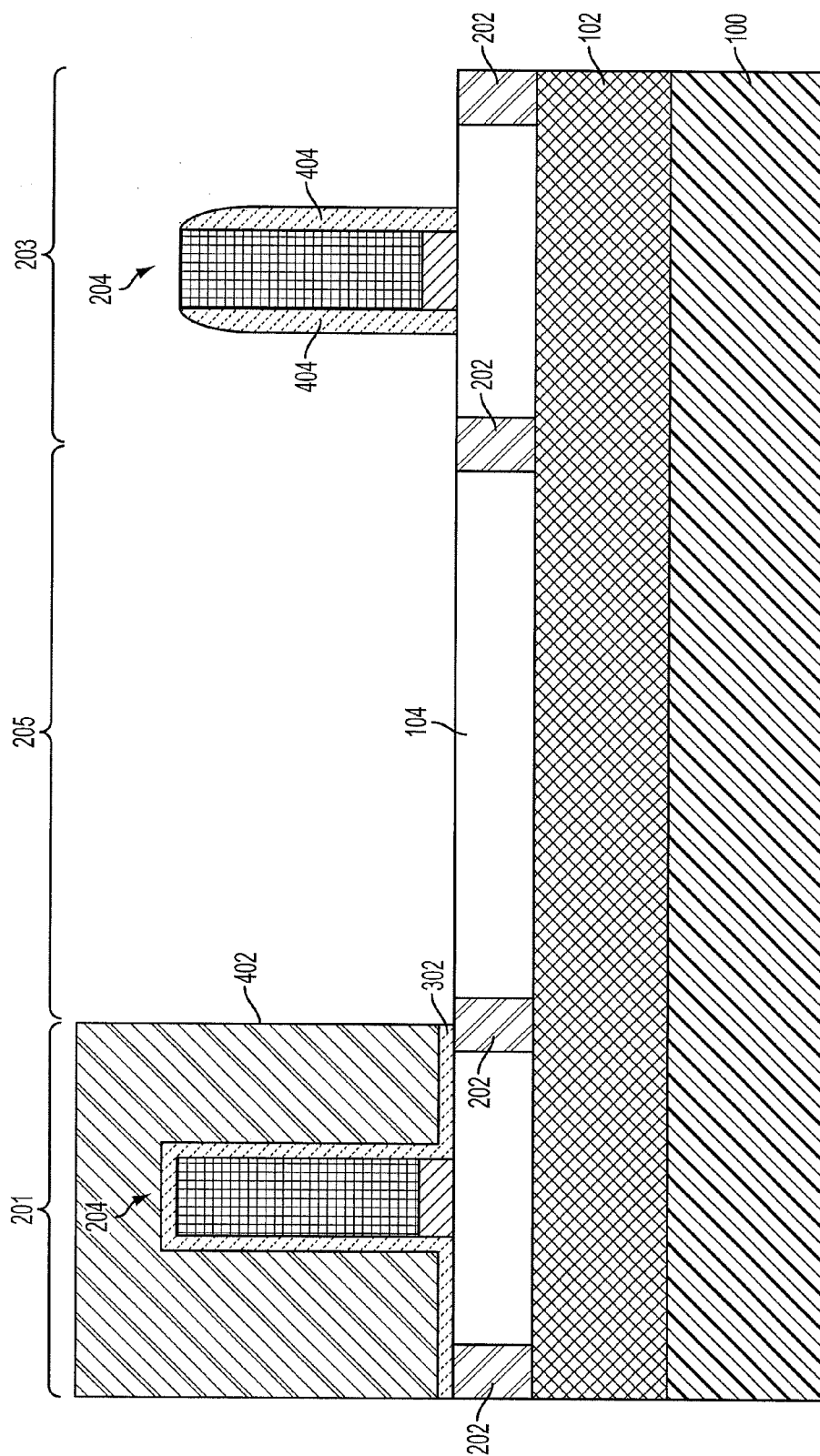


FIG. 4

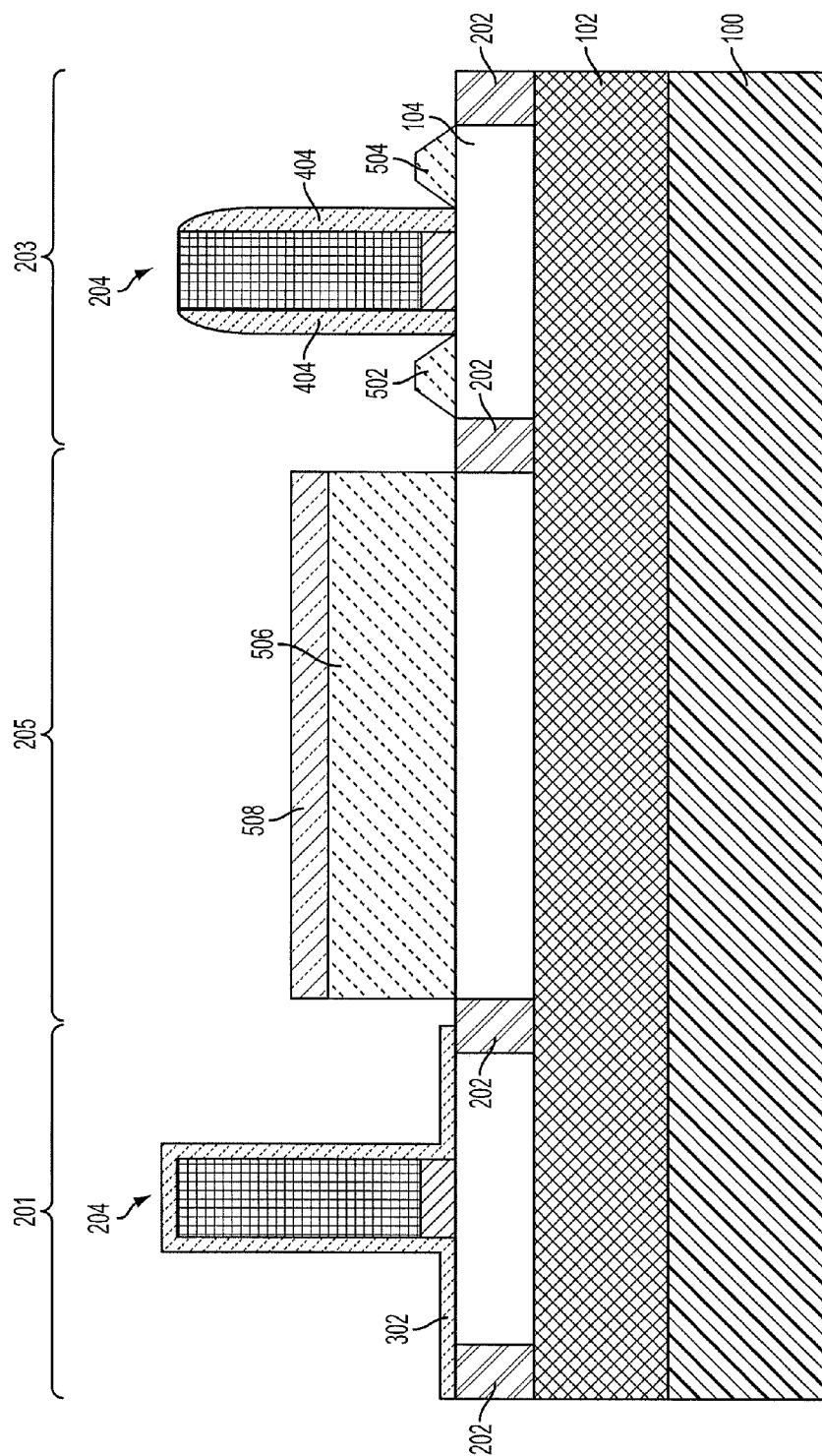


FIG. 5

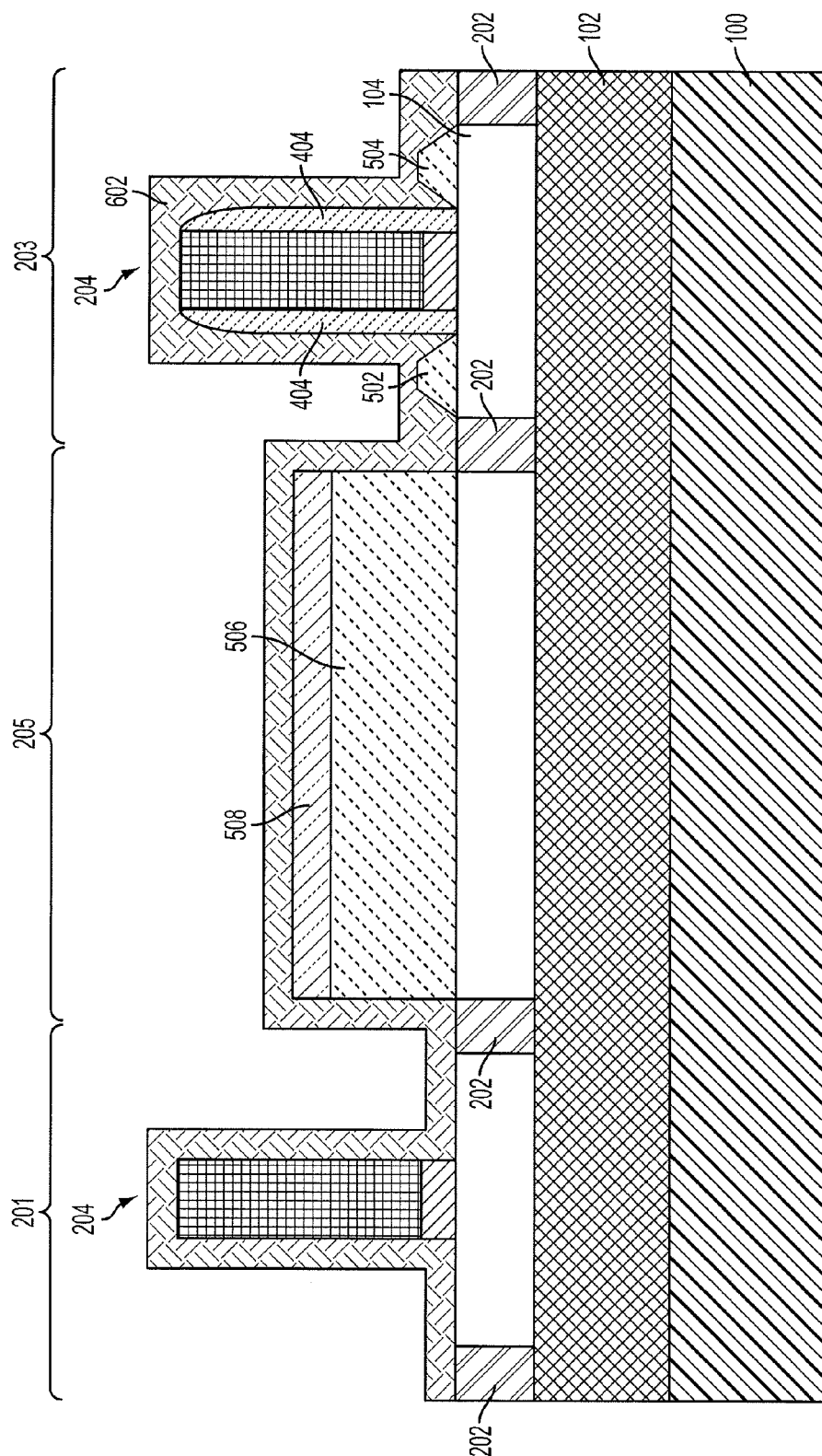


FIG. 6



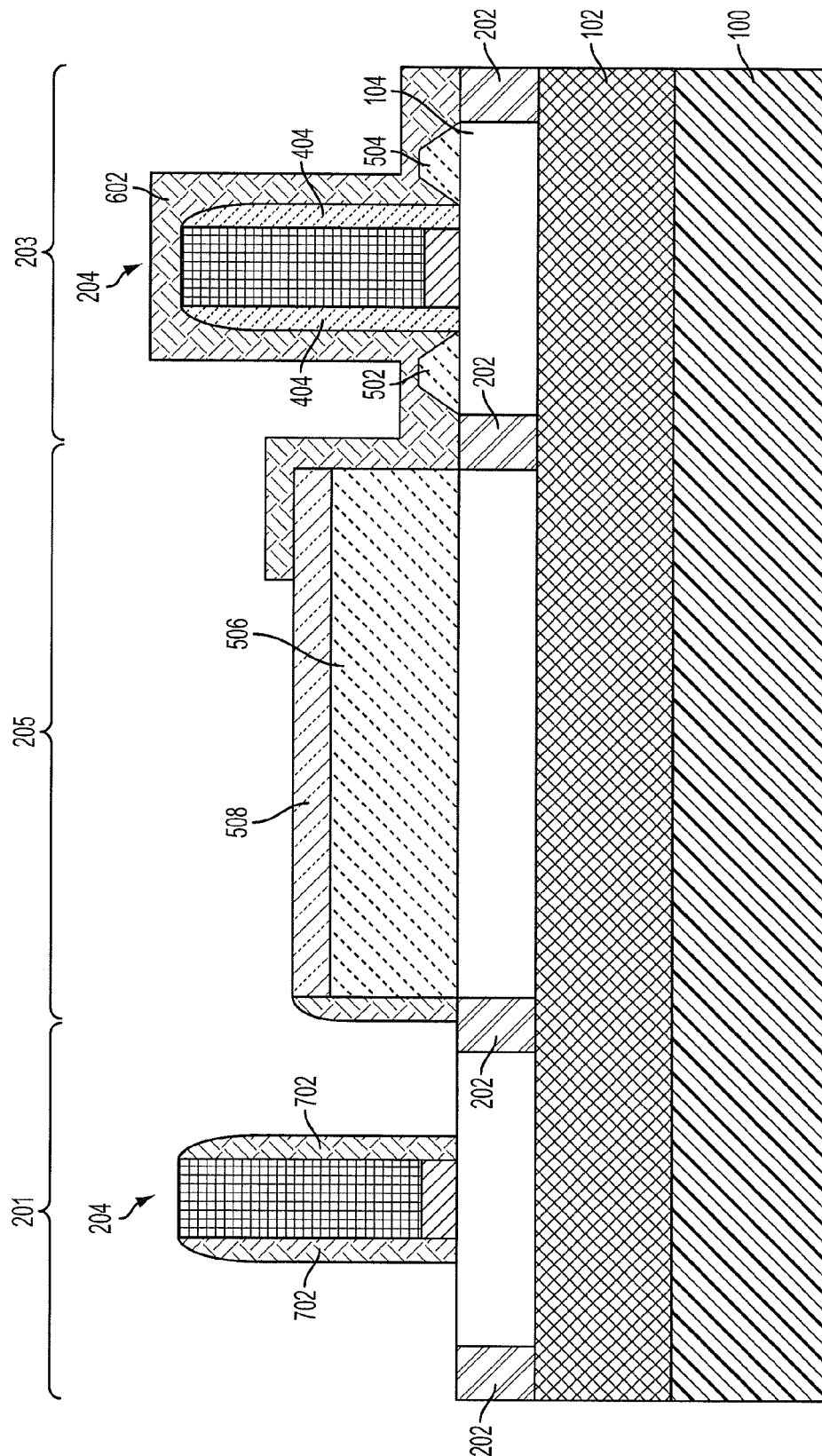


FIG. 7

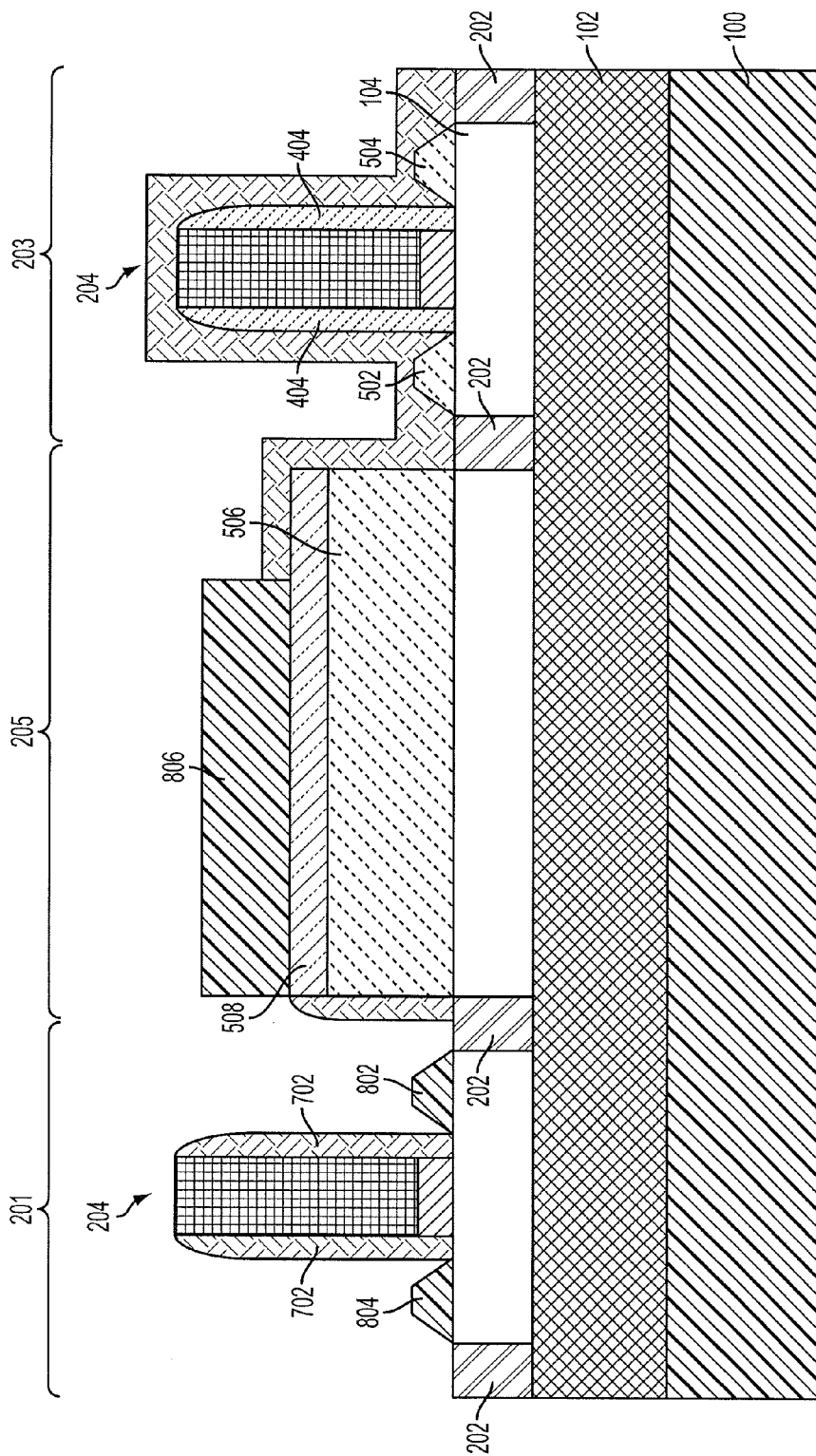


FIG. 8

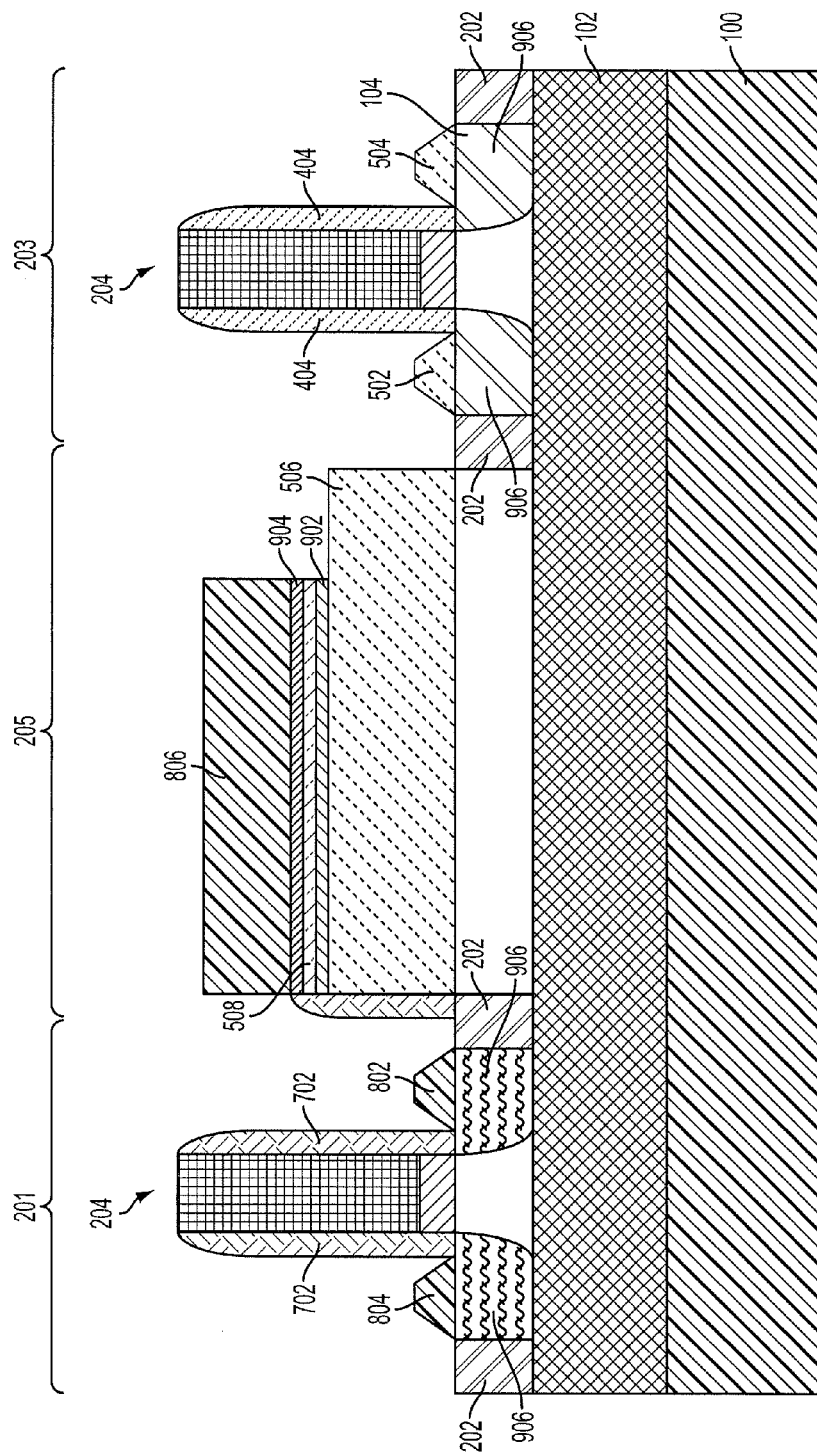


FIG. 9

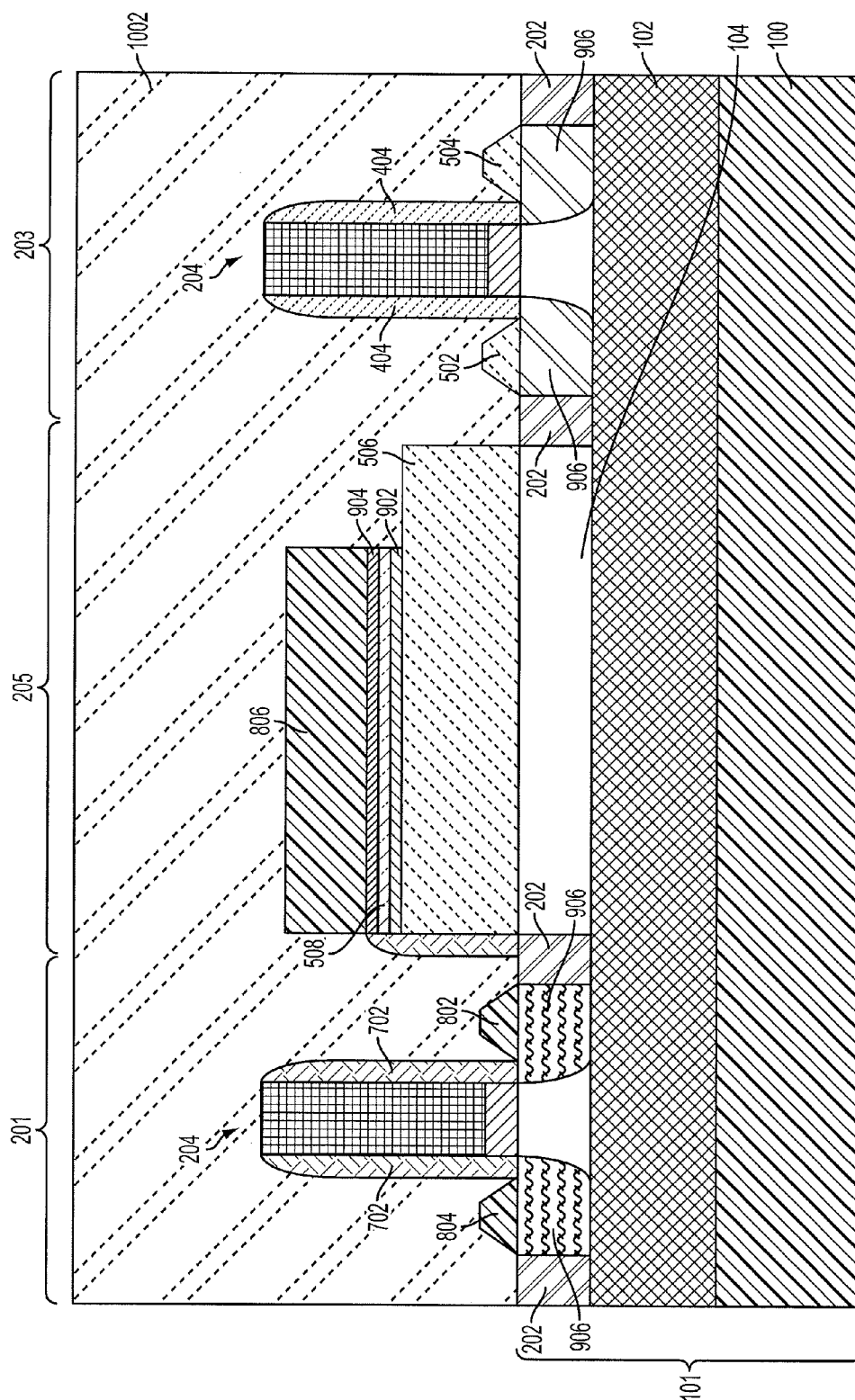


FIG. 10

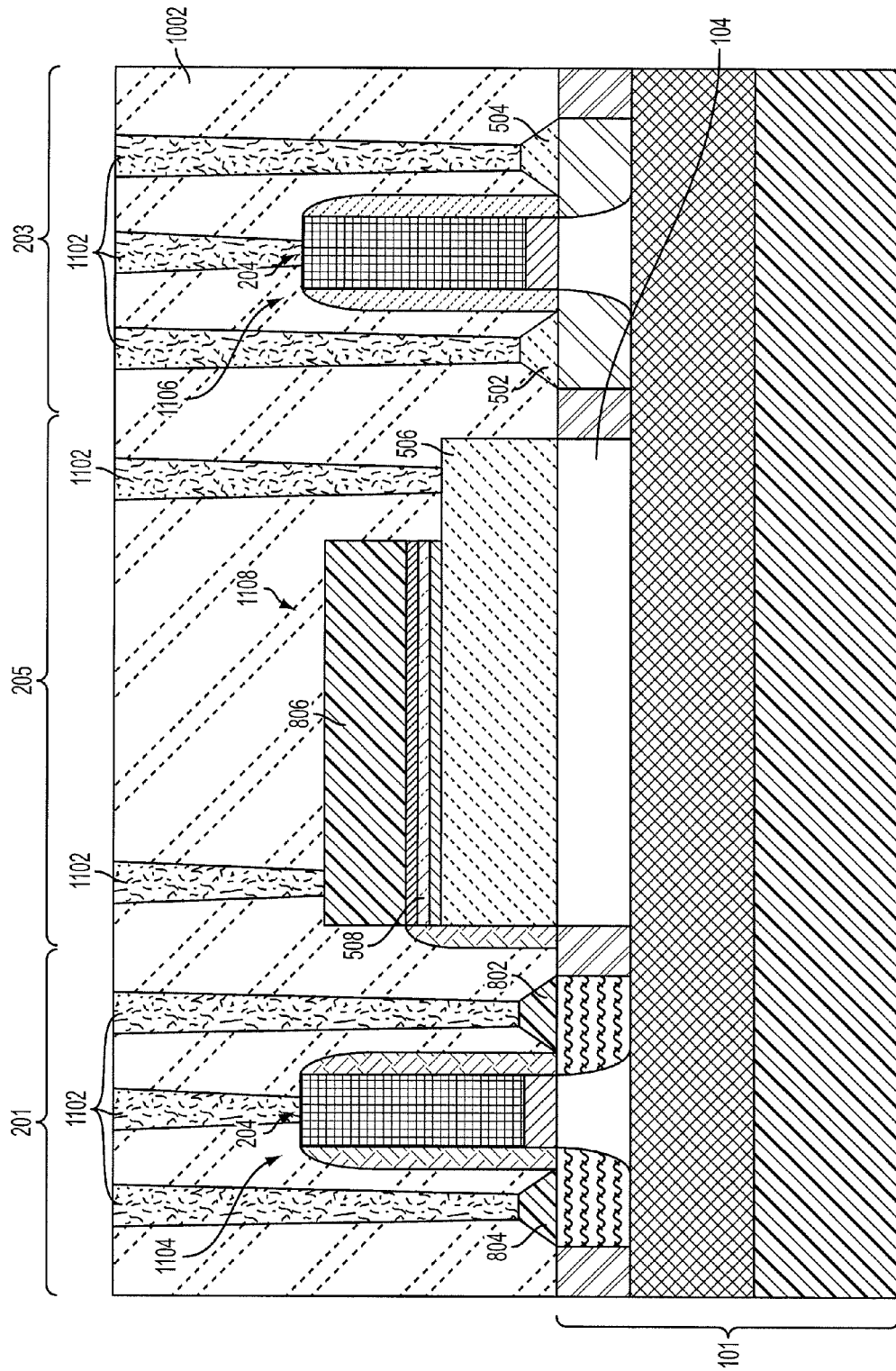


FIG. 11

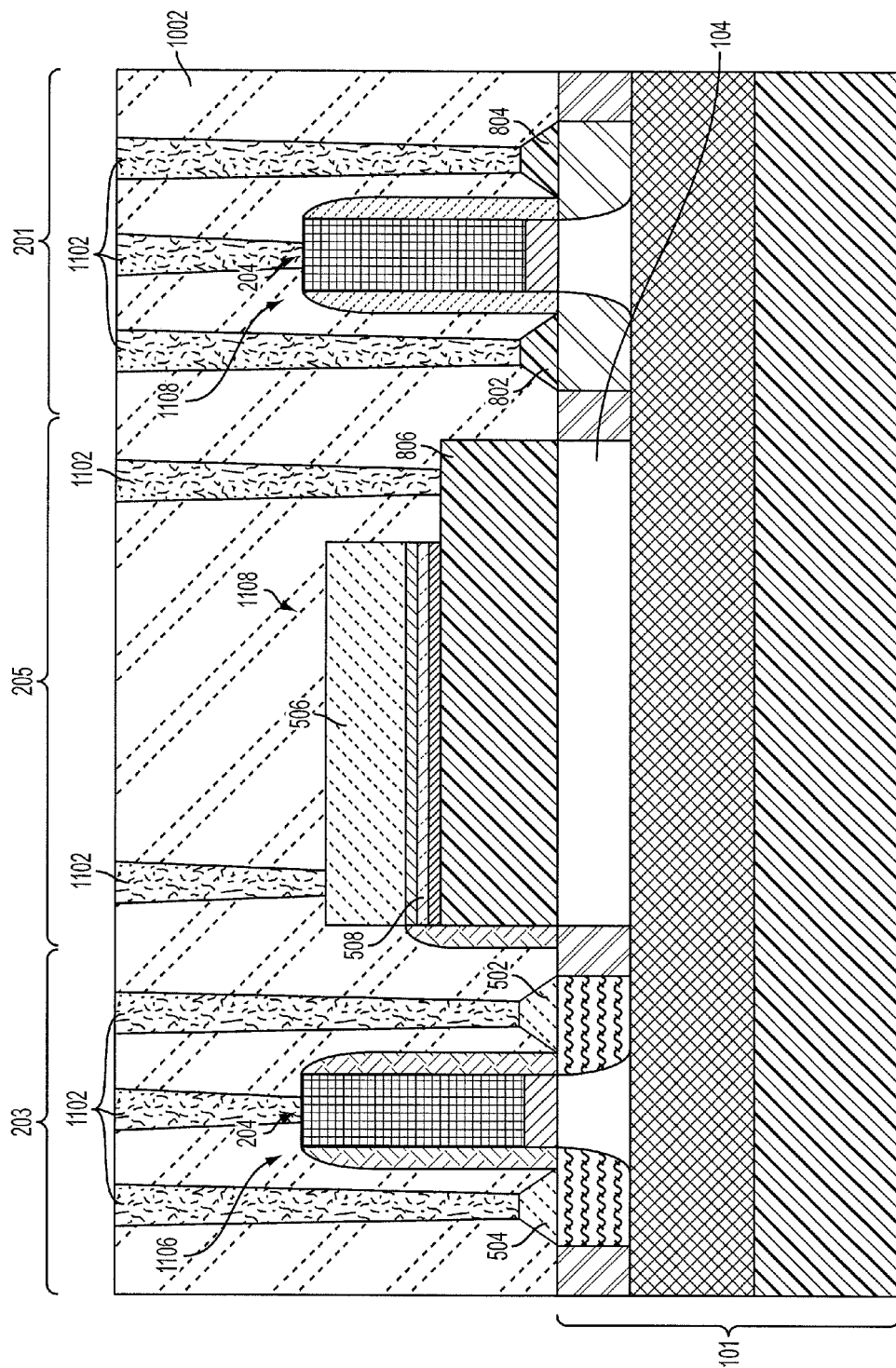


FIG. 12

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**INTEGRATED CIRCUIT DIODE****CROSS-REFERENCE TO RELATED APPLICATION**

This application is a continuation of U.S. patent application Ser. No. 13/104,542, filed May 10, 2011, now U.S. Pat. No. 8,482,078, the disclosure of which is incorporated by reference herein in its entirety.

**FIELD**

The present invention relates generally to integrated circuits, and more specifically, to fabricating diodes and resultant diode structures in integrated circuits.

**DESCRIPTION OF RELATED ART**

Diodes may be formed on semiconductor substrates that may include other devices such as field effect transistors (FETs). Previous diodes were fabricated by implanting dopants or ions in relatively thick semiconductor layers to improve the characteristics of the diodes. These types of diodes often exhibited undesirably high leakage currents due to defects in the implants. As the thickness of the semiconductor layers in FET devices continues to be reduced, the use of a relatively thick semiconductor layer for diodes continues to be problematic.

**SUMMARY**

According to one embodiment of the present invention, a method includes forming an isolation regions in a silicon substrate to define an first field effect transistor (FET) region, a second FET region, and a diode region, forming a first gate stack in the first FET region and a second gate stack in the second FET region, forming a layer of spacer material over the second FET region and the second gate stack, forming a first source region and a first drain region in the first FET region and a first diode layer in the diode region using a first epitaxial growth process, forming a hardmask layer over the first source region, the first drain region, the first gate stack and a portion of the first diode layer, and forming a second source region and a second drain region in the first FET region and a second diode layer on the first diode layer using a second epitaxial growth process.

According to another embodiment of the present invention, a method includes forming an isolation regions in a silicon substrate to define an first field effect transistor (FET) region and a diode region, forming a first gate stack in the first FET region, forming a first source region and a first drain region in the first FET region and a first diode layer in the diode region using a first epitaxial growth process, forming a hardmask layer over the first source region, the first drain region, the first gate stack and a portion of the first diode layer, and forming a second diode layer on the first diode layer using a second epitaxial growth process.

According to yet another embodiment of the present invention, a semiconductor device includes a first FET disposed on a substrate having a source region and a drain region, the source region and the drain region of the first FET including a first epitaxial material, a diode disposed on the substrate having a first layer disposed on the substrate, an insulator layer disposed on the first layer, and a third layer disposed on the insulator layer, the first layer including the first epitaxial

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material, the insulator layer including an undoped epitaxial material, and the third layer including a second epitaxial material.

Additional features and advantages are realized through the techniques of the present invention. Other embodiments and aspects of the invention are described in detail herein and are considered a part of the claimed invention. For a better understanding of the invention with the advantages and the features, refer to the description and to the drawings.

**BRIEF DESCRIPTION OF THE SEVERAL VIEWS OF THE DRAWINGS**

The subject matter which is regarded as the invention is particularly pointed out and distinctly claimed in the claims at the conclusion of the specification. The foregoing and other features, and advantages of the invention are apparent from the following detailed description taken in conjunction with the accompanying drawings in which:

FIG. 1 illustrates a side cut-away view of a semiconductor substrate arrangement.

FIG. 2 illustrates the resultant structure following the formation of isolation regions in the substrate of FIG. 1.

FIG. 3 illustrates the resultant structure following the deposition of a spacer material layer.

FIG. 4 illustrates the resultant structure following the removal of portions of the spacer material layer.

FIG. 5 illustrates the formation of a source region, a drain region, and a diode layer.

FIG. 6 illustrates the formation of a hardmask layer.

FIG. 7 illustrates the resultant structure following the removal of portions of the hardmask layer.

FIG. 8 illustrates the formation of a source region, a drain region, and a diode layer.

FIG. 9 illustrates the resultant structure following the removal of portions of the hardmask layer.

FIG. 10 illustrates the formation of a capping layer.

FIG. 11 illustrates an exemplary embodiment of the resultant structure of FET and diode devices following the formation of conductive vias in the capping layer.

FIG. 12 illustrates an alternate exemplary embodiment of an arrangement of FET and diode devices.

**DETAILED DESCRIPTION**

Diodes are often fabricated in semiconductor devices by implanting dopants or ions in a layer of the semiconductor substrate. The layer of semiconductor substrate is often relatively thick to improve the electrical characteristics of the diodes. However, a thick semiconductor substrate layer may be undesirable when fabricating FET devices on the semiconductor substrate. The methods and resultant structures described below offer a process for forming a diode and FET devices on a semiconductor substrate layer with a relatively thin thickness using epitaxial material growth processes.

FIGS. 1-11 illustrate an exemplary method and resultant structure for forming a diode and FET devices on a silicon substrate. In this regard, FIG. 1 illustrates a side cut-away view of a semiconductor substrate arrangement **101** that includes a bulk substrate layer **100**, a buried insulating layer (e.g., buried oxide (BOX)) layer **102** disposed on the substrate layer **100**, and a semiconductor on insulator (SOI) layer **104** disposed on the BOX layer **102**. The SOI layer **104** may comprise any semiconducting material including, but not limited to Si, strained Si, SiC, SiGe, SiGeC, Si alloys, Ge, Ge alloys, GaAs, InAs, and InP, or any combination thereof. The SOI layer **104** may be thinned to a desired thickness by

planarization, grinding, wet etch, dry etch, oxidation followed by oxide etch, or any combination thereof. One method of thinning the SOI layer **104** is to oxidize the silicon by a thermal dry or wet oxidation process, and then wet etch the oxide layer using a hydrofluoric acid mixture. This process can be repeated to achieve the desired thickness. In one embodiment, the SOI layer **104** may be extremely thin SOI (ETSOI) with a thickness ranging from 1.0 nm to 10.0 nm. In another embodiment, the SOI layer **104** has a thickness ranging from 1.0 nm to 5.0 nm. In a further embodiment, the SOI layer **104** has a thickness ranging from 3.0 nm to 8.0 nm. The substrate layer **100** may be a semiconducting material including, but not limited to Si, strained Si, SiC, SiGe, SiGeC, Si alloys, Ge, Ge alloys, GaAs, InAs, InP as well as other III/V and II/VI compound semiconductors.

The insulating layer **102** that may be present underlying the SOI layer **104** and atop the substrate layer **100** may be formed by implanting a high-energy dopant into the substrate **100** and then annealing the structure to form a buried insulating layer, i.e., the insulating layer **102**. In another embodiment, the insulating layer **102** may be deposited or grown prior to the formation of the SOI layer **104**. In yet another embodiment, the substrate **5** may be formed using wafer-bonding techniques, where a bonded wafer pair is formed utilizing glue, adhesive polymer, or direct bonding. The insulating layer **102** may include a single or multiple layers of insulating materials such as oxide, nitride, oxynitride, high-k dielectric, etc.

FIG. 2 illustrates the resultant structure following the formation of isolation regions **202** in the SOI layer **104**. The isolation regions **202** may be defined by, for example, a lithographic patterning and etching process that removes portions of the SOI layer **104**, down to the top of the BOX layer **102** to define the isolation regions **202**. The isolation regions **202** may be formed by, for example, depositing a dielectric material such as a silicon oxide or an oxynitride material in the defined isolation regions **202**. A liner material (not shown) such as, for example, a high-K dielectric, oxide, or nitride material may be formed prior to depositing the dielectric material. The isolation regions **202** partially define an n-type FET (nFET) region **201**, a p-type FET (pFET) region **203**, and a diode region **205** in the SOI layer **104**. In the illustrated embodiment, gate stacks **204** have been formed in the nFET region **201** and the pFET region **203**. The gate stacks **204** may include any number of layers of gate material such as a gate dielectric material **206** and gate conductor material layer **208** and a capping layer that may include, for example, a polysilicon material. The gate stacks **204** may be formed using any appropriate methods that may include, for example, any variety of photolithographic patterning, material etching, and material deposition methods.

Though the illustrated embodiment includes gate stacks **204** that may be used to form FET devices, in alternate embodiments, the gate stacks **204** may be formed from a material such as, for example, polysilicon to form dummy gate stacks having a similar size and shape as the gate stacks **204**. Dummy gate stacks may be used to define a channel region in the SOI layer **104**. In exemplary fabrication methods, the dummy gate stacks may be formed to define the channel region and allow subsequent fabrication processes to be performed. Once the subsequent fabrication processes have been performed, the dummy gate stacks may be removed and replaced with the gate stacks **204** that are used in the FET devices. For illustrative purposes, the illustrated embodiments include gate stacks **204**. However, alternate embodiments may include the formation of dummy gate stacks instead of the illustrated gate stacks **204** that may be

subsequently removed and replaced with gate stacks similar to the gate stacks **204** in follow on processes.

FIG. 3 illustrates the resultant structure following the deposition of a spacer material layer **302** over the exposed portions of the isolation regions **202**, the SOI layer **104**, and the gate stacks **204**. The spacer material layer **302** may include, for example, a nitride material or an oxide material.

FIG. 4 illustrates the resultant structure following the removal of portions of the spacer material layer **302**. In this regard, a masking material **402** has been deposited and patterned over the spacer material layer **302** in the nFET region **201**. An etching process such as, for example, anisotropic etching process (e.g., reactive ion etch (RIE)) has been performed to remove exposed portions of the spacer material layer **302**. The anisotropic etching process may form the spacers **404** along side walls of the gate stack **204** in the pFET region **203**.

FIG. 5 illustrates the formation of a raised source region **502** and a raised drain region **504** in the pFET region **203**, as well as a first doped diode layer **506** in the diode region **205**. In this regard, the masking material **402** (of FIG. 4) has been removed. The source and drain regions **502** and **504** and the first doped diode layer **506** are formed using an epitaxial growth process that forms a silicon material such as, for example, SiGe or Si on exposed portions of the SOI layer **104**. The Si material is doped with p-type ions such as, for example, boron (B) or aluminum (Al) during the epitaxial growth process (i.e., in situ doped) such that the resultant source and drain regions **502** and diode layer **506** include p-type ions. The loading effect of the epitaxial growth process results in a thicker growth of epitaxy material in the larger exposed region of the SOI layer **104** (the diode region **205**) as opposed to the smaller exposed regions of the SOI layer **104** (the pFET region **203**). Thus, the first doped diode layer **506** is thicker than the source and drain regions **502** and **504**. In the illustrated embodiment, an undoped layer of silicon material (e.g., Si or SiGe) has been formed on the diode layer **506** to define an undoped diode layer **508**. The undoped diode layer **508** may be formed, for example, during the epitaxial growth process after ambient dopants in the epitaxial chamber have been consumed in the formation of the source and drain regions **502** and **504** and the first doped diode layer **506**. The continuation of the epitaxial growth process without ambient dopants forms the undoped diode layer **508**. In some embodiments, a thin undoped layer of Si material (not shown) may form on the source and drain regions **502** and **504** in the epitaxial growth process. An undoped silicon formation on the source and drain regions **502** and **504** may be consumed during a subsequent salicidation process that will be explained in further detail below.

FIG. 6 illustrates the formation of a hardmask layer **602** that may include, for example, a nitride or oxide material. In the illustrated embodiment, the spacer material layer **302** (of FIG. 3) has been removed with a selective etching process prior to the formation of the hardmask layer **602** such that the hardmask layer **602** is formed over the exposed portions of the SOI layer **104** in the nFET region **201**, the isolation regions **202**, the undoped diode layer **508**, the source and drain regions **502** and **504**, and the gate stacks **204**. In an alternate exemplary method, the spacer material layer **302** may be left in place, and the spacer material layer the hardmask layer **602** may be formed over the spacer material layer **302** as well.

FIG. 7 illustrates the resultant structure following the removal of portions of the hardmask layer **602**. In this regard, portions of the hardmask layer **602** in the pFET region **203** and portions of the diode region **205** may be protected by, for example, a photolithographic masking material. The exposed



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portions of the hardmask layer **602** may be removed using, for example, an anisotropic etching process (e.g., RIE) to expose portions of the SOI layer in the nFET region **201** and portions of the undoped diode layer **508**. The anisotropic etching process may result in the formations of spacers **702** along side-  
walls of the gate stack **204** in the nFET region **201**. As discussed above, in an alternate embodiment, the hardmask layer **602** may be formed over portions of the spacer material layer **302** in the nFET region **201**. In such an embodiment, follow-  
ing the removal of portions of the hardmask layer **602**, the exposed portions of the spacer material layer **302** in the nFET region **201** may be removed using a subsequent etching process to expose portions of the SOI layer **104** in the nFET region **201**.

FIG. **8** illustrates the formation of a raised source region **802** and a raised drain region **804** in the nFET region **201**, as well as a second doped diode layer **806** in the diode region **205**. The source and drain regions **802** and **804** and the second doped diode layer **806** are formed using an epitaxial growth process similar to the epitaxial growth process used to form the source and drain regions **502** and **504** and the first doped diode layer **506** described above. However, the source and drain regions **802** and **804** and the second doped diode layer **806** may be formed from, for example, epitaxially grown Si or SiC, and are in situ-doped with an n-type dopant such as, for example, phosphorus (P) or arsenic (As). The loading effect of the epitaxial growth process results in a diode layer that has a greater thickness than the source and drain regions **802** and **804**.

FIG. **9** illustrates the resultant structure following the removal of portions of the hardmask layer **602** using, for example, an isotropic etching process. A lithographic masking and etching process may be used to remove exposed portions of the undoped diode layer **508** to expose portions of the first doped diode layer **506**. An annealing process may be performed that forms source and drain extension regions **906** in the SOI layer **104**. The annealing process may form a lightly n-type doped region **904** and a lightly doped p-type region **902** in the undoped diode layer **508** by driving n-type diode layer **806** and p-type ions from the first doped diode layer **506** into adjacent portions of the undoped diode layer **508**. A self-aligned silicidation (salicidation) process may be performed to form a silicide material (not shown) over exposed portions of the source and drain regions **502**, **504**, **802**, and **804**; and the first and second doped diode layers **506** and **806**.

FIG. **10** illustrates the formation of a capping layer **1002** that may include, for example, an oxide material over the exposed features in the nFET region **201**, the diode region **205**, and the pFET region **203**.

FIG. **11** illustrates an exemplary embodiment of the resultant structure following the formation of conductive vias **1102** in the capping layer **1002**. The vias **1102** may be formed by, for example, a lithographic patterning and etching process that forms cavities in the capping layer **1002** that expose portions of the source and drain regions **502**, **504**, **802**, and **804**; the gate stacks **204**; and the first and second doped diode layers **506** and **806**. A salicidation process may be performed to form a silicide material (not shown) in the exposed regions if, for example, the silicide material has not been formed in a previous process. The cavities in the capping layer **1002** may be filled with a conductive material such as, for example, tungsten (W) and/or copper (Cu) to form the vias **1102**.

The resultant structure includes an nFET device **1104** formed on the SOI layer **104** in the nFET region **201**, a pFET device **1106** formed on the SOI layer **104** in the pFET region **203** and a PIN (p-type-intrinsic (undoped)-n-type) diode

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device **1108** formed on the SOI layer **104** in the diode region **205**. The PIN diode device **1108** includes a p-type layer (the first doped diode layer **506**) formed on the SOI layer **104**, an intrinsic layer (the undoped diode layer **508**) formed on the diode layer **506**, and an n-type layer (the second doped diode layer **806**) formed on the undoped diode layer **508**.

The illustrated exemplary methods include forming the p-type doped source and drain regions **502** and **504** (of the pFET device **1106**) and the p-type doped diode layer **506** prior to forming the n-type doped source and drain regions **802** and **804** (of the nFET device **1106**) and the n-type doped diode layer **806**. Alternate embodiments may include, for example, forming the n-type doped source and drain regions **802** and **804** and the n-type doped diode layer **806** prior to forming the p-type doped source and drain regions **502** and **504** (of the pFET device **1106**) and the p-type doped diode layer **506**. In such alternate exemplary embodiments, similar processes described above would be used. FIG. **12** illustrates an alternate exemplary embodiment of an arrangement similar to the arrangement described above in FIG. **11**, however the resultant structure includes an n-type diode layer **806** disposed on the SOI layer **104**, an undoped layer **508** formed on the n-type diode layer **806** and a p-type diode layer **506** formed on the undoped layer **508**. Alternatively, the layer **508** may be lightly doped due to the dopant diffusion from the doped layers **806** and **506**.

As discussed above, alternate embodiments may include the formation of dummy gate stacks having a similar size, shape, and location as the gate stacks **204** as opposed to forming the gate stacks **204** as shown. In such alternate embodiments, the dummy gate stacks (not shown) would be removed prior to or after the annealing process and replaced with actual gate stacks similar to the gate stacks **204**. In this regard, a masking process may, for example, be used to protect the source and drain regions **502**, **504**, **802**, and **804**, and the layers in the diode region **205**. The dummy gate stacks may then be removed and replaced with the gate stacks **204** using any variety of photolithographic patterning, etching, and deposition processes.

The terminology used herein is for the purpose of describing particular embodiments only and is not intended to be limiting of the invention. As used herein, the singular forms “a”, “an” and “the” are intended to include the plural forms as well, unless the context clearly indicates otherwise. It will be further understood that the terms “comprises” and/or “comprising,” when used in this specification, specify the presence of stated features, integers, steps, operations, elements, and/or components, but do not preclude the presence or addition of one or more other features, integers, steps, operations, element components, and/or groups thereof.

The corresponding structures, materials, acts, and equivalents of all means or step plus function elements in the claims below are intended to include any structure, material, or act for performing the function in combination with other claimed elements as specifically claimed. The description of the present invention has been presented for purposes of illustration and description, but is not intended to be exhaustive or limited to the invention in the form disclosed. Many modifications and variations will be apparent to those of ordinary skill in the art without departing from the scope and spirit of the invention. The embodiment was chosen and described in order to best explain the principles of the invention and the practical application, and to enable others of ordinary skill in the art to understand the invention for various embodiments with various modifications as are suited to the particular use contemplated.

The flow diagrams depicted herein are just one example. There may be many variations to this diagram or the steps (or operations) described therein without departing from the spirit of the invention. For instance, the steps may be performed in a differing order or steps may be added, deleted or modified. All of these variations are considered a part of the claimed invention.

While the preferred embodiment to the invention had been described, it will be understood that those skilled in the art, both now and in the future, may make various improvements and enhancements which fall within the scope of the claims which follow. These claims should be construed to maintain the proper protection for the invention first described.

The invention claimed is:

1. A semiconductor device, comprising:  
isolation regions formed in a semiconductor substrate to define a first field effect transistor (FET) region, a second FET region, and a diode region;  
a first gate stack formed in the first FET region and a second gate stack formed in the second FET region;  
a first epitaxial source region and a first epitaxial drain region formed in the first FET region and a first epitaxial diode layer formed in the diode region; and  
a second epitaxial source region and a second epitaxial drain region formed in the second FET region and a second epitaxial diode layer formed on the first epitaxial diode layer.
2. The semiconductor device of claim 1, wherein the first epitaxial source region, the first epitaxial drain region, and

portions of the first epitaxial diode layer include p-type dopants, and the second epitaxial source region, the second epitaxial drain region, and the second epitaxial diode layer include n-type dopants.

3. The semiconductor device of claim 1, wherein the first epitaxial source region, the first epitaxial drain region, and portions of the first epitaxial diode layer include n-type dopants, and the second epitaxial source region, the second epitaxial drain region, and the second epitaxial diode layer include p-type dopants.

4. The semiconductor device of claim 1, wherein the first epitaxial diode layer has a greater thickness than the first epitaxial source region.

5. The semiconductor device of claim 1, wherein the second epitaxial source region and the second epitaxial drain region comprise a silicon germanium material.

6. The semiconductor device of claim 1, further comprising a doped region formed in the first epitaxial diode layer and an undoped region disposed on the doped region of the first epitaxial diode layer.

7. The semiconductor device of claim 1, wherein the first epitaxial diode layer is formed from a same semiconductor material as the first epitaxial source and drain regions, and the second epitaxial diode layer is formed from a same semiconductor material as the second epitaxial source and drain regions.

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